Intention Number: 10812416 Johns: 30-Mar-2004 AH-polytype gallium nitride-based semiconductor device on a 4H-polytype substrate Tetsuzo Ueda Tetsuzo Ueda Michael E. Fogarty/Kimberly Pollard rney Docket Number: 43890-673 las Large Entity ity under 35 USC 111(a) Filling Fees
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Request for continued examination	1801	1	810	810
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